TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

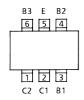
# **TA4100F**

UHF VHF RF, MIX Application

#### **Features**

- High  $f_T$ . ( $f_T = 5 \text{ GHz}$ )
- Differential circuit is composed of 3 transistors.

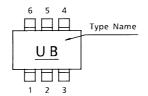
#### Pin Assignment (top view)

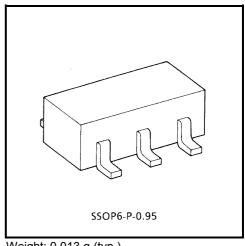


C ... COLLECTOR

B ... BASE ... EMITTER

#### Marking





Weight: 0.013 g (typ.)

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## **Maximum Ratings (Ta = 25°C)**

Characteristic	Symbol	Rating	Unit	
Collector-base voltage	$V_{CBO}$	10	V	
Collector-emitter voltage	$V_{CEO}$	5	V	
Collector current	I <sub>C</sub>	15 (Note 1)	mA	
		30 (Note 2)	IIIA	
Total power dissipation	P <sub>D</sub> (Note3)	300	mW	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	

Note 1: Q1, Q2 Note 2: Q3

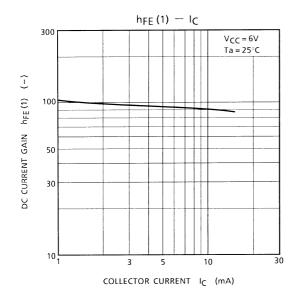
Note 3: When mounted on the glass epoxy board of 2.5  $\text{cm}^2 \times 1.6 \text{ t}$ 

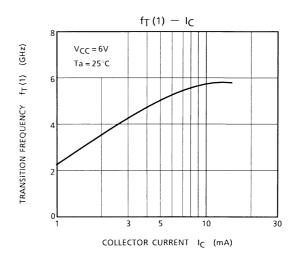
## **Electrical Characteristics (Ta = 25°C)**

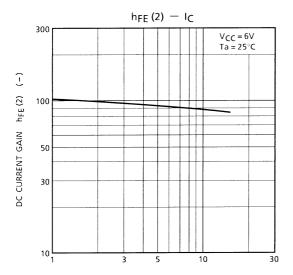
Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector-emitter voltage	V <sub>CEO</sub> (1)	_	$I_{C1} = 1.0 \text{ mA},$ $(I_{B3} = 1 \text{ mA})$ (Note 4)	5	-	-	V
	V <sub>CEO</sub> (2)	_	$I_{C2} = 1.0 \text{ mA},$ $(I_{B3} = 1 \text{ mA})$ (Note 5)	5	-	-	
	V <sub>CEO</sub> (3)	_	$I_{B1} (I_{C3} = 1.0 \text{ mA})$ (Note 6)	5	_	_	
DC Current gain	h <sub>FE</sub> (1)	_	$V_{C1} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 4)	50	100	160	
	h <sub>FE</sub> (2)	_	$V_{C2} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 5)	50	100	160	_
	h <sub>FE</sub> (3)	_	$V_{B1} (V_{C3}) = 6 V,$ $I_{B1} (I_{C3}) = 10 \text{ mA}$ (Note 6)	70	140	250	
Transition Frequency	f <sub>T</sub> (1)	_	$V_{C1} = 6 \text{ V}, I_{C1} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 4)	3.5	5.0	7.0	
	f <sub>T</sub> (2)	_	$V_{C2} = 6 \text{ V}, I_{C2} = 5 \text{ mA}, (I_{B3} = 1 \text{ mA})$ (Note 5)	3.5	5.0	7.0	GHz
	f <sub>T</sub> (3)	_	$V_{B1} (V_{C3}) = 4 V,$ $I_{B1} (I_{C3}) = 10 \text{ mA}$ (Note 6)	3.5	5.0	7.0	

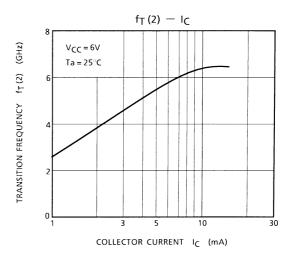
Note 4: Characteristics of Q1 Note 5: Characteristics of Q2 Note 6: Characteristics of Q3

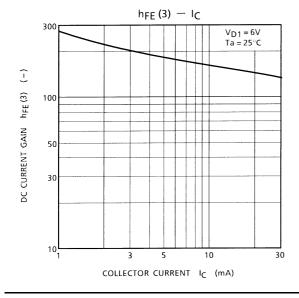
## **Equivalent Circuit**

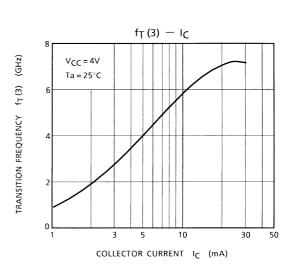








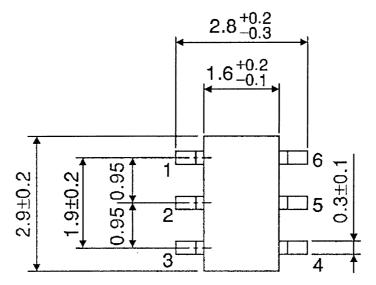


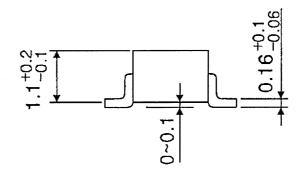




## **Package Dimensions**

SSOP6-P-0.95 Unit: mm





Weight: 0.013g (Typ.)